Title of the Invention: Resistive switching memory cell
Abstract Title: Resistive switching memory cell

A resistive random access memory (ReRAM) device is provided. The ReRAM device includes a first electrode, a first resistive structure in contact with the first electrode, a dielectric layer in contact with the first resistive structure, and a second resistive structure in contact with the dielectric layer. The second resistive structure includes a resistive material layer and a high work function metal core. The ReRAM device also includes a second electrode in contact with the second resistive structure.